November 1999 Revised November 2000

FAIRCHILD

SEMICONDUCTOR

74LVTH646 Low Voltage Octal Transceiver/Register with 3-STATE Outputs

General Description

The LVTH646 consists of registered bus transceiver circuits, D-type flip-flops, and control circuitry providing multiplexed transmission of data directly from the input bus or from the internal storage registers. Data on the A or B bus will be loaded into the respective registers on the LOW-to-HIGH transition of the appropriate clock pin (CPAB or CPBA). (See Functional Description)

The LVTH646 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

The bus transceivers are designed for low-voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVTH646 is fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining low power dissipation.

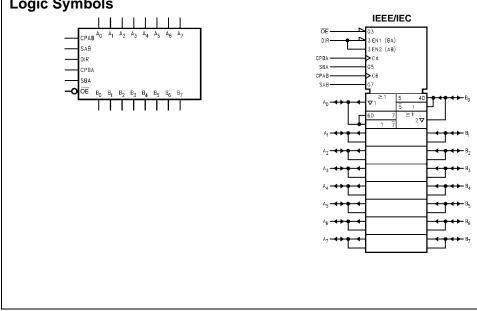
Features

- Input and output interface capability to systems at $5VV_{CC}$
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink -32 mA/+64 mA
- Functionally compatible with the 74 series 646
- Latch-up performance exceeds 500 mA
- ESD performance: Human-body model > 2000V Machine model > 200V Charged-device model > 1000V

Ordering Code:

Order Number	Package Number	Package Description					
74LVTH646WM	M24B	24-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300 Wide					
74LVTH646MTC	MTC24	24-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide					
Devices also available	Devices also available in Tape and Reel. Specify by appending letter suffix "X" to the ordering code.						

Logic Symbols



© 2000 Fairchild Semiconductor Corporation DS012017

74LVTH646

$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Connection Diagram								
	SAB DIR A ₀ - A ₁ - A ₂ - A ₃ - A ₄ - A ₅ - A ₆ - A ₇ -	2 2 3 2 4 2 5 2 6 7 7 9 9 - 10 -	23 CPBA 22 SBA 21 OE 20 B ₀ 19 B ₁ 18 B ₂ 17 B ₃ 16 B ₄ 15 B ₅ 14 B ₆						

Pin Descriptions

Pin Names	Description
A ₀ -A ₇	Data Register A Inputs
	Data Register A Outputs
B ₀ -B ₇	Data Register B Inputs
	Data Register B Outputs
СРАВ, СРВА	Clock Pulse Inputs
SAB, SBA	Transmit/Receive Inputs
OE	Output Enable Input
DIR	Direction Control Input

Truth Table

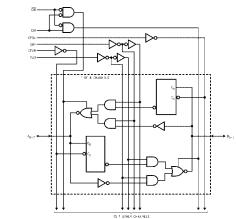
(Note 1)

Inputs						Data I/O		Function
OE	DIR	CPAB	СРВА	SAB	SBA	A ₀ –A ₇	B ₀ –B ₇	Function
Н	Х	H or L	H or L	Х	Х			Isolation
н	Х	~	Х	Х	Х	Input	Input	Clock A _n Data into A Register
н	Х	Х	~	Х	Х			Clock B _n Data into B Register
L	Н	Х	Х	L	Х			An to Bn—Real Time (Transparent Mode)
L	Н	~	Х	L	Х	Input Output		Clock An Data into A Register
L	н	H or L	Х	н	Х			A Register to B _n (Stored Mode)
L	н	~	Х	н	Х			Clock A_n Data into A Register and Output to B_n
L	L	Х	Х	Х	L			B _n to A _n —Real Time (Transparent Mode)
L	L	Х	~	Х	L	Output	lanut	Clock B _n Data into B Register
L	L	х	H or L	Х	н	Output	Input	B Register to A _n (Stored Mode)
L	L	Х	~	Х	Н			Clock B_n Data into B Register and Output to A_n

H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial \checkmark = LOW-to-HIGH Transition

Note 1: The data output functions may be enabled or disabled by various signals at the $\overline{\text{OE}}$ and DIR inputs. Data input functions are always enabled; i.e., data at the bus pins will be stored on every LOW-to-HIGH transition of the appropriate clock inputs.

Logic Diagram

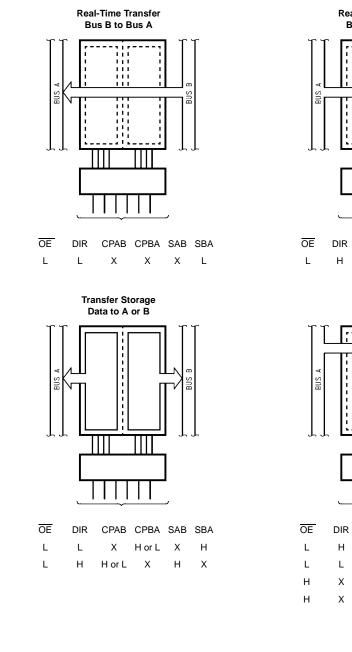


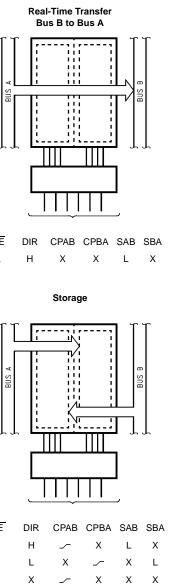
Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Functional Description

In the transceiver mode, data present at the HIGH impedance port may be stored in either the A or B register or both. The select (SAB, SBA) controls can multiplex stored and real-time. The examples below demonstrate the four fundamental busmanagement functions that can be performed.

The direction control (DIR) determines which bus will receive data when \overline{OE} is LOW. In the isolation mode (\overline{OE} HIGH), A data may be stored in one register and/or B data may be stored in the other register. When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two busses, A or B, may be driven at a time.





Х

www.fairchildsemi.com

Х

Х

~

74LVTH646

۸ L .:. Dati Ma

Symbol	Parameter	Value	Conditions	Units
V _{CC}	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		V
Vo	DC Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in HIGH or LOW State (Note 3)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
I _O	DC Output Current	64	V _O > V _{CC} Output at HIGH State	mA
		128	V _O > V _{CC} Output at LOW State	mA
I _{CC}	DC Supply Current per Supply Pin	±64		mA
I _{GND}	DC Ground Current per Ground Pin	±128		mA
T _{STG}	Storage Temperature	-65 to +150		°C

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I _{OH}	HIGH Level Output Current		-32	mA
I _{OL}	LOW Level Output Current		64	IIIA
T _A	Free-Air Operating Temperature	-40	85	°C
$\Delta t/\Delta V$	Input Edge Rate, V _{IN} = 0.8V–2.0V, V _{CC} = 3.0V	0	10	ns/V

Note 2: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied. Note 3: I_{O} Absolute Maximum Rating must be observed.

			V _{CC}	T _A =-40°C	T _A =-40°C to +85°C		
Symbol	Parameter	(V)	Min	Max	Units	Conditions	
V _{IK}	Input Clamp Diode Voltage		2.7		-1.2	V	I _I = -18 mA
VIH	Input HIGH Voltage		2.7-3.6	2.0		V	$V_0 \le 0.1V$ or
V _{IL}	Input LOW Voltage		2.7-3.6		0.8	v	$V_O \ge V_{CC} - 0.1V$
V _{OH}	Output HIGH Voltage		2.7–3.6	V _{CC} - 0.2		V	I _{OH} = -100 μA
			2.7	2.4		V	I _{OH} = -8 mA
			3.0	2.0		V	I _{OH} = -32 mA
V _{OL}	Output LOW Voltage		2.7		0.2	V	I _{OL} = 100 μA
			2.7		0.5	V	I _{OL} = 24 mA
			3.0		0.4	V	I _{OL} = 16 mA
			3.0		0.5	V	I _{OL} = 32 mA
		3.0		0.55	V	I _{OL} = 64 mA	
I _{I(HOLD)}	Bushold Input Minimum Drive		3.0	75		μΑ	$V_{I} = 0.8V$
				-75		μΑ	$V_{I} = 2.0V$
I _{I(OD)}	Bushold Input Over-Drive Current to Change State		3.0	500		μΑ	(Note 4)
				-500		μΑ	(Note 5)
կ	Input Current		3.6		10	μΑ	$V_{I} = 5.5V$
		Control Pins	3.6		±1	μΑ	$V_I = 0V \text{ or } V_{CC}$
		Data Pins	3.6		-5	μΑ	$V_I = 0V$
					1	μΑ	$V_I = V_{CC}$
I _{OFF}	Power Off Leakage Current		0		±100	μΑ	$0V \le V_1 \text{ or } V_0 \le 5.5V$
I _{PU/PD}	Power up/down 3-STATE Output Current		0–1.5V		±100	μA	$V_O = 0.5V$ to 3.0V $V_I = GND$ or V_{CC}
IOZL	3-STATE Output Leakage Curre	ent	3.6		-5	μA	$V_{\rm O} = 0.0 \text{V}$
I _{OZH}	3-STATE Output Leakage Curre		3.6		5	μA	$V_0 = 3.6V$
I _{OZH} +	3-STATE Output Leakage Curre		3.6		10	μΑ	$V_{CC} < V_{O} \le 5.5V$
I _{CCH}	Power Supply Current		3.6		0.19	mA	Outputs HIGH
ICCL	Power Supply Current		3.6		5	mA	Outputs LOW
I _{CCZ}	Power Supply Current		3.6		0.19	mA	Outputs Disabled
Iccz+	Power Supply Current		3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$
JUL							Outputs Disabled
ΔI_{CC}	Increase in Power Supply Curre	ent	3.6		0.2	mA	One Input at V _{CC} – 0.6V
	(Note 6) external driver must source at least t						Other Inputs at V _{CC} or GNI

Note 4: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 5: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 6: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 7)

Symbol	Parameter	V_{CC} $T_A = 25^{\circ}C$		Units	Conditions			
Cymbol	i arameter	(V)	Min	Тур	Max	Onits	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF},~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 8)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 8)	

Note 7: Characterized in SOIC package. Guaranteed parameter, but not tested.

Note 8: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

74LVTH646

74LVTH646

AC Electrical Characteristics

			T _A = -40°C	C to +85°C		
Symbol	Parameter	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF},~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$				
Symbol	Falanietei	$V_{CC} = 3.$	$3V \pm 0.3V$	V _{CC} :	Units	
		Min	Max	Min	Max	
f _{MAX}	Maximum Clock Frequency	150		150		MHz
t _{PLH}	Propagation Delay Data to Output	1.8	5.7	1.8	6.3	
t _{PHL}	Clock to A or B	1.8	5.0	1.8	5.6	ns
t _{PLH}	Propagation Delay Data to Output	1.3	4.6	1.3	5.0	ns
t _{PHL}	Data to A or B		4.6	1.3	5.3	ns
t _{PLH}	Propagation Delay Data to Output	1.5	5.5	1.5	6.5	ns
t _{PHL}	SBA or SAB to A or B	1.5	5.5	1.5	6.3	115
t _{PZH}	Output Enable Time	1.1	5.7	1.1	6.8	
t _{PZL}	OE to A or B	1.1	6.3	1.1	7.3	ns
t _{PHZ}	Output Disable Time	1.9	5.7	2.3	6.1	ns
t _{PLZ}	OE to A or B	1.6	5.5	2.3	5.9	115
t _{PZH}	Output Enable Time	1.3	6.1	1.3	6.7	ns
t _{PZL}	DIR to A or B	1.3	6.7	1.3	7.7	115
t _{PHZ}	Output Disable Time	1.5	6.2	1.5	7.1	ns
t _{PLZ}	DIR to A or B	1.5	5.6	1.5	6.3	115
t _W	Pulse Duration Clock HIGH or LOW	3.3		3.3		ns
t _S	Setup Time A or B Before Clock, Data HIGH	1.2		1.5	1	
	A or B Before Clock, Data LOW	1.6		2.2		ns
t _H	Hold Time A or B after Clock	0.8		0.8	1	ns
t _{OSHL}	Output to Output Skew (Note 9)		1.0		1.0	ns
t _{OSLH}			1.0		1.0	nS

Note 9: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}).

Capacitance (Note 10)

Symbol	Parameter	Conditions	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 0V, V_I = 0V \text{ or } V_{CC}$	4	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.0V$, $V_{O} = 0V$ or V_{CC}	8	pF
Note 10: Ca	pacitance is measured at frequency f - 1 MHz, per l	MIL-STD-883B Method 3012		

Note 10: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.

